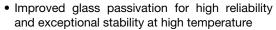


Medium Power Phase Control Thyristors (Stud Version), 10 A



PRIMARY CHARACTERISTICS				
I _{T(AV)}	10 A			
V _{DRM} /V _{RRM}	100 V, 200 V, 400 V, 600 V, 800 V, 1000 V, 1200 V			
V _{TM}	1.75 V			
I _{GT}	60 mA			
T _J	-65 °C to +125 °C			
Package	TO-48 (TO-208AA)			
Circuit configuration	Single SCR			

FEATURES





- High dl_F/dt and dV/dt capabilities
- Standard package
- Low thermal resistance
- · Metric threads version available
- Types up to 1200 V V_{DRM}/V_{RRM}
- Designed and qualified for industrial and consumer level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

TYPICAL APPLICATIONS

- Medium power switching
- · Phase control applications

MAJOR RATINGS AND CHARACTERISTICS					
PARAMETER	TEST CONDITIONS	VALUES	UNITS		
1		10	А		
I _{T(AV)}	T _C	85	°C		
I _{T(RMS)}		25	А		
I _{TSM}	50 Hz	225	А А		
	60 Hz	240			
l ² t	50 Hz	255	A2-		
1-1	60 Hz	233	A ² s		
V _{DRM} /V _{RRM}		100 to 1200	V		
t _q	Typical	110	μs		
T _J		-65 to +125	°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS							
TYPE NUMBER	VOLTAGE CODE	V _{DRM} /V _{RRM} , MAXIMUM REPETITIVE PEAK AND OFF-STATE VOLTAGE ⁽¹⁾ V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK VOLTAGE ⁽²⁾ V	I_{DRM}/I_{RRM} MAXIMUM AT T _J = T _J MAXIMUM mA			
	10	100	150	20			
	20	200	300				
	40	400	500				
VS-10RIA	60	600	700	10			
	80	800	900	10			
	100	1000	1100				
	120	1200	1300				

Notes

⁽¹⁾ Units may be broken over non-repetitively in the off-state direction without damage, if dl/dt does not exceed 20 A/µs

 $[\]ensuremath{^{(2)}}$ For voltage pulses with $t_p \leq 5 \ ms$



ABSOLUTE MAXIMUM RAT	TINGS					
PARAMETER	SYMBOL		TEST CONDITIONS		VALUES	UNITS
Maximum average on-state current	I	190° conducti	180° conduction, half sine wave		10	Α
at case temperature	I _{T(AV)}	100 Conducti	on, nan sine wave		85	°C
Maximum RMS on-state current	I _{T(RMS)}				25	Α
		t = 10 ms	No voltage		225	
Maximum peak, one-cycle	L	t = 8.3 ms	reapplied		240	Α
non-repetitive surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		190	A
		t = 8.3 ms	reapplied	Sinusoidal half wave,	200	
Maximum I ² t for fusing		t = 10 ms	No voltage	initial $T_J = T_J$ maximum	255	- A ² s
	l ² t	t = 8.3 ms	reapplied		233	
	i-r	t = 10 ms	100 % V _{RRM} reapplied		180	
		t = 8.3 ms			165	
Maximum I ² √t for fusing	I²√t	t = 0.1 to 10 m	t = 0.1 to 10 ms, no voltage reapplied		2550	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π x	(16.7 % x π x $I_{T(AV)} < I < \pi$ x $I_{T(AV)}$), $T_J = T_J$ maximum		1.10	V
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)}),$	$T_J = T_J \text{ maximum}$		1.39	V
Low level value of on-state slope resistance	r _{t1}	(16.7 % x π x	(16.7 % x π x $I_{T(AV)}$ < I < π x $I_{T(AV)}$), $T_J = T_J$ maximum		24.3	mΩ
High level value of on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)}), T_J = T_J \text{ maximum}$		16.7	11152	
Maximum on-state voltage	V_{TM}	I_{pk} = 32 A, T_J = 25 °C, t_p = 10 ms sine pulse		1.75	V	
Maximum holding current	I _H	T. = 25 °C 22	odo supply 12 V ro	esistivo load	130	mΛ
Typical latching current	ΙL	1j = 25 C, all	ode supply 12 V re	SISTING TOAU	200	mA

SWITCHING					
PARAMETER		SYMBOL	TEST CONDITIONS	VALUES	UNITS
	$V_{DRM} \le 600 \text{ V}$			200	
Maximum rate of rise V _{DRM} ≤ 800 V		41 /d+	$T_J = T_J$ maximum, $V_{DM} = Rated V_{DRM}$ $Gate pulse = 20 V, 15 Ω, t_p = 6 μs, t_r = 0.1 μs maximum$ $I_{TM} = (2 x rated dl/dt) A$	180	- A/μs
of turned-on current	urned-on current $V_{DRM} \le 1000 \text{ V}$			160	
$V_{DRM} \le 1600 \text{ V}$,	150	
Typical turn-on time		t _{gt}	$T_J = 25$ °C, at rated V_{DRM}/V_{RRM} , $T_J = 125$ °C	0.9	
Typical reverse recovery time		t _{rr}	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200 \mu s$, $dI_F/dt = -10 A/\mu s$	4	μs
Typical turn-off time		tq	$T_J = T_J$ maximum, $I_{TM} = I_{T(AV)}$, $t_p > 200~\mu$ s, $V_R = 100~V$, $dI_F/dt = -10~A/\mu$ s, $dV/dt = 20~V/\mu$ s linear to 67 % V_{DRM} , gate bias 0 V to 100 W	110	μο

Note

• $t_q = 10 \mu s$ up to 600 V, $t_q = 30 \mu s$ up to 1600 V available on special request

BLOCKING				
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS
Maximum critical rate of rise	dV/dt	$T_J = T_J$ maximum linear to 100 % rated V_{DRM}	100	V/µs
of off-state voltage	uv/ut	$T_J = T_J$ maximum linear to 67 % rated V_{DRM}	300 (1)	ν/μ5

Note

 $^{(1)}$ Available with: $dV/dt = 1000 V/\mu s$, to complete code add S90 i.e. 10RIA120S90



TRIGGERING					
PARAMETER	SYMBOL	TE	ST CONDITIONS	VALUES	UNITS
Maximum peak gate power	P _{GM}	T - T movimum		8.0	W
Maximum average gate power	P _{G(AV)}	$T_J = T_J$ maximum		2.0	۷V
Maximum peak positive gate current	I_{GM}	$T_J = T_J$ maximum		1.5	Α
Maximum peak negative gate voltage	-V _{GM}	$T_J = T_J$ maximum		10	V
	I _{GT}	T _J = -65 °C	Maximum required gate trigger current/voltage are the lowest value which will trigger all units 6 V anode to cathode applied	90	mA
DC gate current required to trigger		T _J = 25 °C		60	
		T _J = 125 °C		35	
		T _J = -65 °C		3.0	V
DC gate voltage required to trigger	V_{GT}	T _J = 25 °C		2.0	
		T _J = 125 °C		1.0	
DC gate current not to trigger	I_{GD}	T _J = T _J maximum, V _{DRM} = Rated value		2.0	mA
DC gate voltage not to trigger	V_GD	$T_J = T_J$ maximum, $V_{DRM} = Rated value$	Maximum gate current/voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode applied	0.2	V

THERMAL AND MECHANICAL SPECIFICATIONS					
PARAMETER	SYMBOL	TEST CONDITIONS	VAL	VALUES	
Maximum operating junction and storage temperature range	T _J , T _{Stg}		-65 to	+125	°C
Maximum thermal resistance, junction to case	R _{thJC}	DC operation	1.	1.85	
Maximum thermal resistance, case to heat sink	R _{thCS}	Mounting surface, smooth, flat and greased 0.35		35	K/W
			TO NUT	TO DEVICE	
			20 (27.5)	25	lbf ⋅ in
Mounting torque		Lubricated threads (Non-lubricated threads)	0.23 (0.32)	0.29	kgf · m
		(1011) (1211) (111)	2.3 (3.1)	2.8	N · m
Approximate weight			14		g
Approximate weight			0.	49	OZ.
Case style		See dimensions - link at the end of datasheet	TO	-48 (TO-208A	A)

△R _{thJC} CONDUCTION				
CONDUCTION ANGLE	SINUSOIDAL CONDUCTION	RECTANGULAR CONDUCTION	TEST CONDITIONS	UNITS
180°	0.44	0.32		
120°	0.53	0.56		
90°	0.68	0.75	$T_J = T_J$ maximum	K/W
60°	1.01	1.05		
30°	1.71	1.73		

Note

The table above shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC



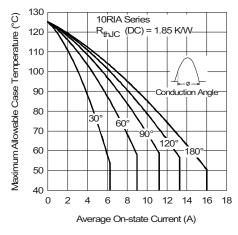


Fig. 1 - Current Ratings Characteristics

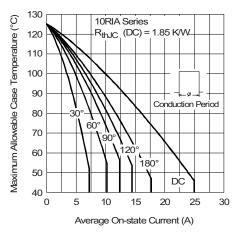


Fig. 2 - Current Ratings Characteristics

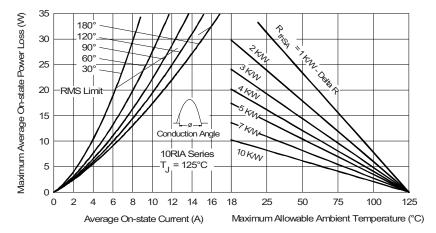


Fig. 3 - On-State Power Loss Characteristics

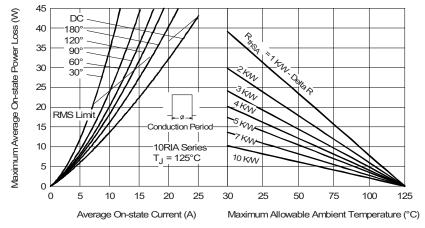


Fig. 4 - On-State Power Loss Characteristics



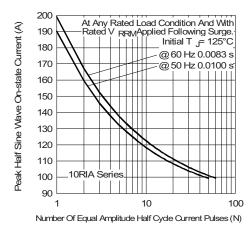


Fig. 5 - Maximum Non-Repetitive Surge Current

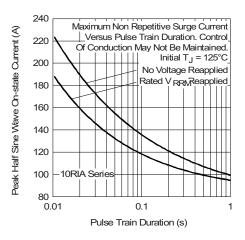


Fig. 6 - Maximum Non-Repetitive Surge Current

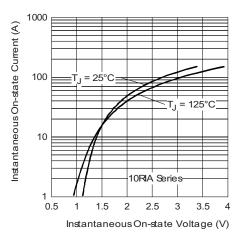


Fig. 7 - Forward Voltage Drop Characteristics

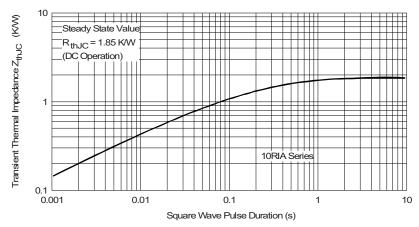


Fig. 8 - Thermal Impedance Z_{thJC} Characteristics



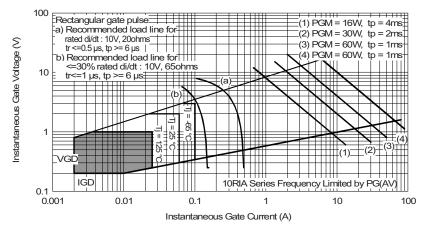
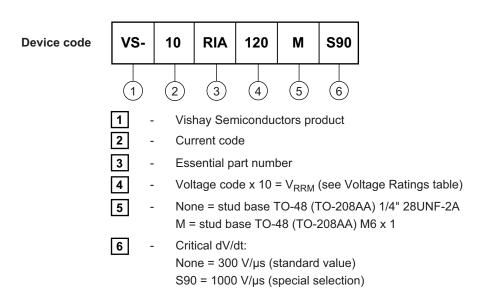


Fig. 9 - Gate Characteristics

ORDERING INFORMATION TABLE

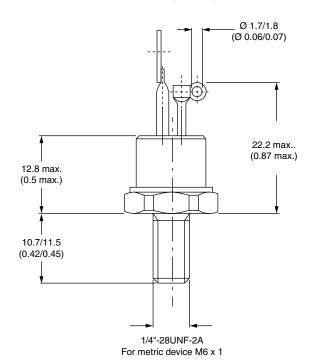


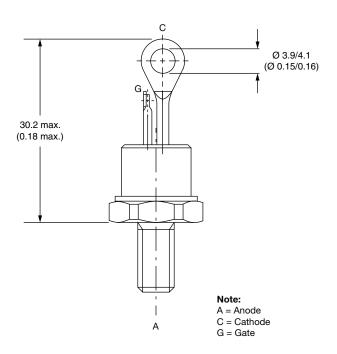
LINKS TO RELAT	ED DOCUMENTS
Dimensions	www.vishay.com/doc?95333

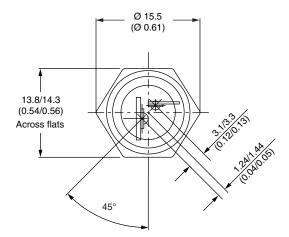


TO-208AA (TO-48)

DIMENSIONS in millimeters (inches)









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